

Dual Wide Bandwidth Operational Amplifier

The MCT4558C combines all of the outstanding features of the MC1458 and, in addition, offers three times the unity gain bandwidth of the industry standard.

- 2.0 MHz Unity Gain Bandwidth Guaranteed
- Internally Compensated
- Short Circuit Protection
- Gain and Phase Match Between Amplifiers
- Low Power Consumption

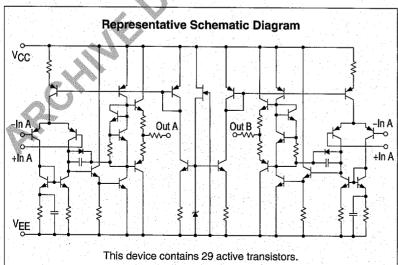
This MCT-prefixed device is intended to be a possible replacement for the similar device with the MC-prefix. Because the MCT device originates from different source material, there may be subtle differences in typical parameter values or characteristic curves. Due to the diversity of potential applications, Motorola can not assure identical performance in all circuits. Motorola recommends that the customer qualify the MCT-prefixed device in each potential application.

MAXIMUM RATINGS (T_A = +25°C, unless otherwise noted.)

Rating	Symbol	Value	Unit
Power Supply Voltages	V _{CC} VEE	+18 -18	Vdc
Input Differential Voltage	V _{ID}	±30	٧
Input Common Mode Voltage (Note 1)	VICM	±15	٧
Output Short Circuit Duration (Note 2)	tsc 🥒	Continuous	
Ambient Temperature Range	TA	0 to +70	°C
Storage Temperature Range	T _{stg}	-55 to +125	°C
Junction Temperature	TJ	150	°C

NOTES: 1. For supply voltages less than ± 15 V, the absolute maximum input voltage is equal to the supply voltage.

2. Short circuit may be to ground or either supply.



CAUTION: These devices do not have internal ESD protection circuitry and are rated as CLASS 1 devices per the ESD test method in Mil-Std-833D. They should be handled using standard ESD prevention methods to avoid damage to the device.

MCT4558C

DUAL WIDE BANDWIDTH OPERATIONAL AMPLIFIER

SEMICONDUCTOR TECHNICAL DATA



P1 SUFFIX PLASTIC PACKAGE CASE 626



D SUFFIX PLASTIC PACKAGE CASE 751 (SO-8)

Output A 1 B VCC Top View) PIN CONNECTIONS 8 VCC Top Output B B G S Inputs B

ORDERING INFORMATION

Device	Tested Operating Temperature Range	Package	
MCT4558CD	T. 001- 7000	SO-8	
MCT4558CPI	$T_A = 0^\circ \text{ to } +70^\circ \text{C}$	Plastic DIP	

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FREQUENCY CHARACTERISTICS ($V_{CC} = +15 \text{ V}, V_{EE} = -15 \text{ V}, T_A = 25^{\circ}\text{C}$)

Characteristic	Symbol	Min	Тур	Max	Unit
Unity Gain Bandwidth	BW	2.0	2.8	-	MHz

ELECTRICAL CHARACTERISTICS (V_{CC} = 15 V, V_{EE} = -15 V, T_A = 25°C, unless otherwise noted.)

1220 11 10 12 11 11 10 (VCC = 10 V, VEE = -10 V, IA = 20 C, I	ATTICOS OLFICI WIS	e noteu.)			
Input Offset Voltage $(R_S \le 10 \text{ k}\Omega)$	V _{IO}	_	2.0	6.0	Væ
Input Offset Current	Ιο		20	200	nA
Input Bias Current (Note 1)	Iβ		80	500	nA
Common Mode Input Voltage Range	VICR	±12	±13	-	V
Large Signal Voltage Gain ($V_O = \pm 10 \text{ V}$, $R_L = 2.0 \text{ k}\Omega$)	Avol	20	200	_	V/mV
Common Mode Rejection (Rg \leq 10 k Ω)	CMR	70	90	_	dB
Supply Voltage Rejection Ratio (Rs \leq 10 k Ω)	PSRR		30	150	μV/V
Output Voltage Swing $ \begin{array}{l} (R_L \geq 10 \; k \Omega) \\ (R_L \geq 2.0 \; k \Omega) \end{array} $	VØ -	±12 ±10	±14 ±13		V
Output Short Circuit Current	Isc	10	20	75	mA
Supply Currents (Both Amplifiers)	ID	_	4.0	5.6	mA
Power Consumption (Both Amplifiers)	PC		70	170	mW
Transient Response (Unity Gain) $ (V_I = 20 \text{ mV}, \text{ R}_L \geq 2.0 \text{ k}\Omega, \text{ C}_L \leq 100 \text{ pF}) \text{ Rise Time} \\ (V_I = 20 \text{ mV}, \text{ R}_L \geq 2.0 \text{ k}\Omega, \text{ C}_L \leq 100 \text{ pF}) \text{ Overshoot} \\ (V_I = 10 \text{ V}, \text{ R}_L \geq 2.0 \text{ k}\Omega, \text{ C}_L \leq 100 \text{ pF}) \text{ Slew Rate} $	tTLH os SR	1.0	0.3 15 1.8		μs % V/μs

ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = -15 V, T_A = T_{high} to T_{low}, [Note 2] unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Input Offset Voltage (R _S \leq 10 k Ω)	VIO		_	7.5	mV
Input Offset Current (T _A = 0° to +70°C)	lιο	_	_	300	nA
Input Bias Current (T _A = 0° to +70°C)	I _{IB}		_	800	nA
Large Signal Voltage Gain ($V_O = \pm 10$ V, $R_L = 2.0$ kΩ)	Avol	15		_	V/mV
Output Voltage Swing $ (R_L \geq 10 \ k\Omega) \\ (R_L \geq 2.0 \ k\Omega) $	Vo	±12 ±10	±14 ±13	_	V
Supply Currents (Both Amplifiers) (TA = Thigh) (TA = Tlow)	D	=	_	5.0 6.7	mA
Power Consumption (Both Amplifiers) (TA = Thigh) (TA = T _{Iow})	PC	_	_	150 200	mW

NOTES: 1. I_{IB} is out of the amplifier due to PNP input transistors.

2. $T_{low} = 0$ °C $T_{high} = +70$ °C

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Figure 1. Power Bandwidth (Large Signal Swing versus Frequency)

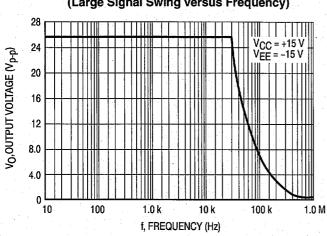


Figure 2. Maximum Output Voltage Swing versus Load Resistance

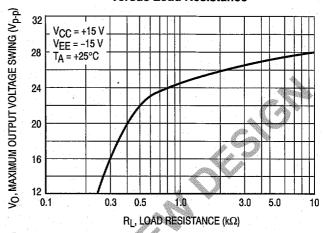


Figure 3. Equivalent Input Noise Voltage versus Frequency

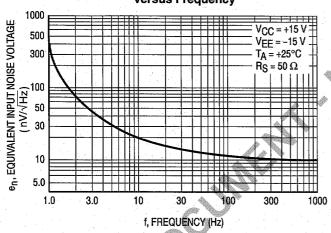


Figure 4. Input Bias Current versus Ambient Temperature

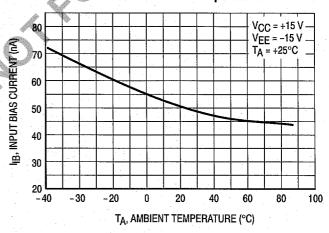


Figure 5. Voltage Gain and Phase versus Frequency

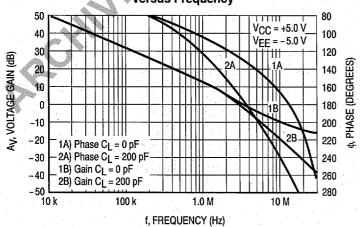
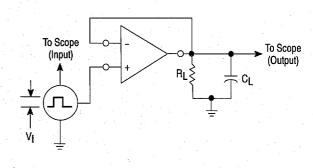
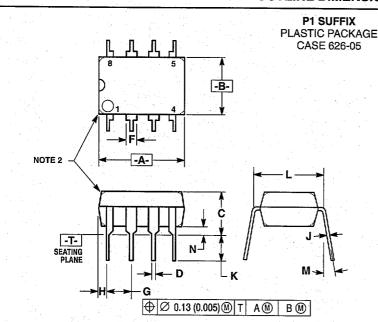


Figure 6. Transient Response Test Circuit



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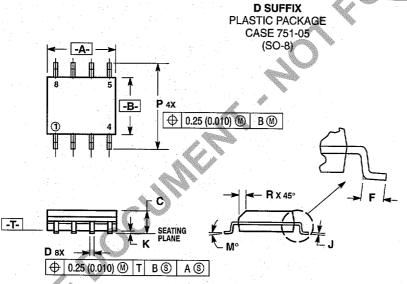
OUTLINE DIMENSIONS



NOTES:

- 1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
 2. PACKAGE CONTOUR OPTIONAL (ROUND OR
- 3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α.	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
C	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54	2.54 BSC		BSC
Н	0.76	1.27	0.030	0.050
J	0.20	0.30	800.0	0.012
K	2.92	3.43	0,115	0.135
L	7.62 BSC		0.300	BSC
	_ 	_ు 10°్	_	10°
_N	0.76	1/01	0.030	0.040



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE
- MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE
- 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
_DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.196
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.2	1.27 BSC		BSC
J	0.18	0.25	0.007	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р.	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

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